30V N-Channel Trench Power MOSFET

General Description

The SJD30N043C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 5V. This device is suitable for use as a wide variety of applications.

Features

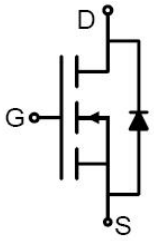
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

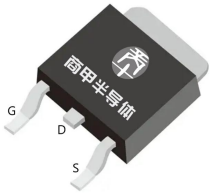
- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(ON)_TYP}$	4.4	mΩ
I_D	88	A
Q_G	33.5	nC



Schematic Diagram



TO-252(DPAK) top view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJD30N043C	SJD30N043C	TO-252	Tape	\	\	2500 Pcs

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	30	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_C=25℃)	88	A
	Drain Current-Continuous(T_C=100℃)	56	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	352	A
P_D	Maximum Power Dissipation(T_C=25℃)	78	W
	Maximum Power Dissipation(T_C=100℃)	31	W
E_{AS}	Avalanche energy (Note 2)	132	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.6	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=30V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1		2.5	V
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		24		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=15A T_J=25℃		4.4	6	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=5V, I_D=10A T_J=25℃		7.2	9.6	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V,V_{GS}=0V, f=1.0MHz		1710		pF
C_{oss}	Output Capacitance			185		pF
C_{rss}	Reverse Transfer Capacitance			170		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		3		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=15V, R_L=1Ω, R_{GEN}=6Ω		10		nS
t_r	Turn-on Rise Time			148		nS
$t_{d(off)}$	Turn-Off Delay Time			40		nS
t_f	Turn-Off Fall Time			18		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=15A		33.5		nC
Q_{gs}	Gate-Source Charge			5		nC
Q_{gd}	Gate-Drain Charge			6.5		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				88	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=15A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=15A, dI/dt=100A/μs		20.5		ns
Q_{rr}	Reverse Recovery Charge	I_F=15A, dI/dt=100A/μs		12.5		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=30V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

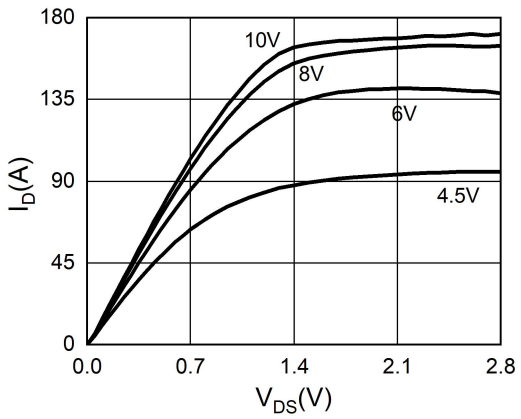


Figure 2. Transfer Characteristics

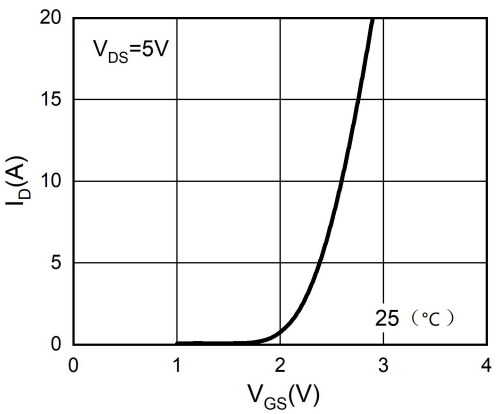


Figure 3. Power Dissipation

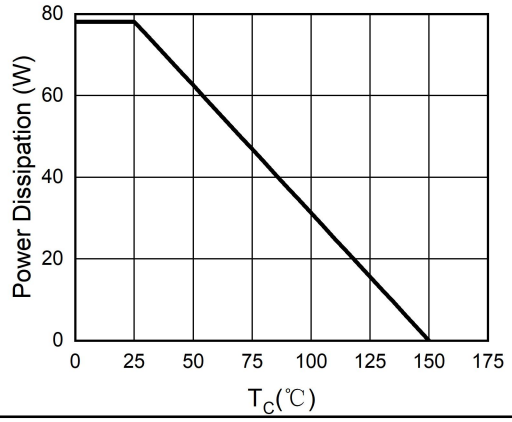


Figure 4. Drain Current

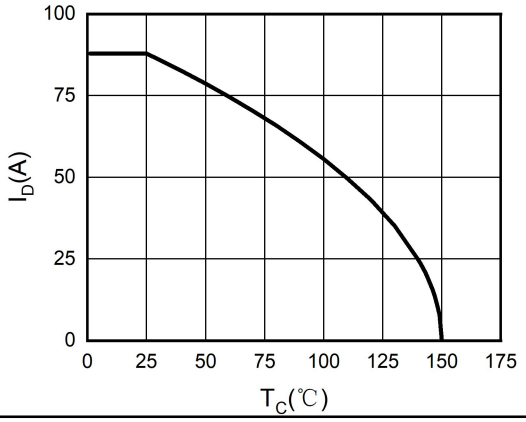


Figure 5. BV_{DSS} vs Junction Temperature

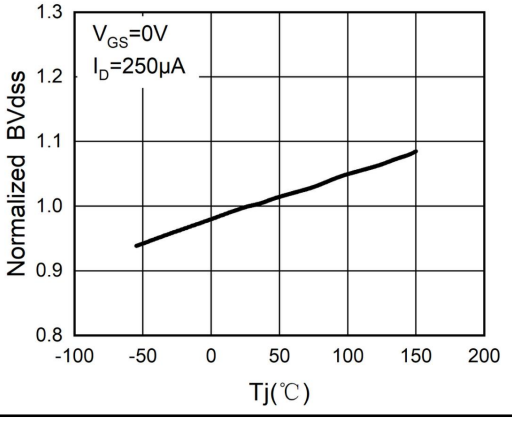
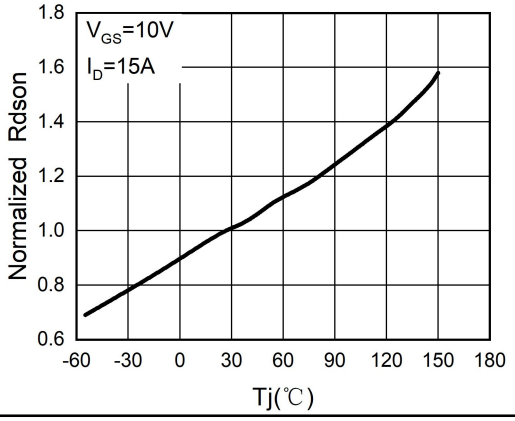


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

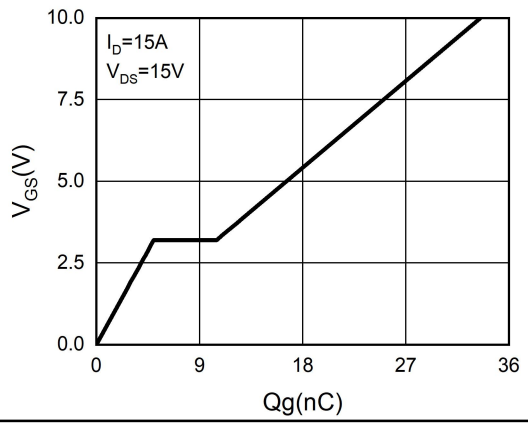


Figure 8. Capacitance

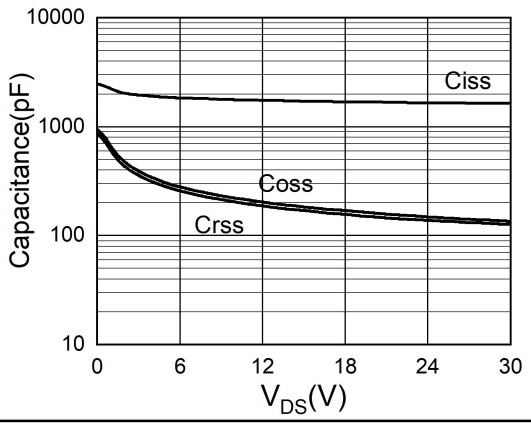


Figure 9. Body-Diode Characteristics

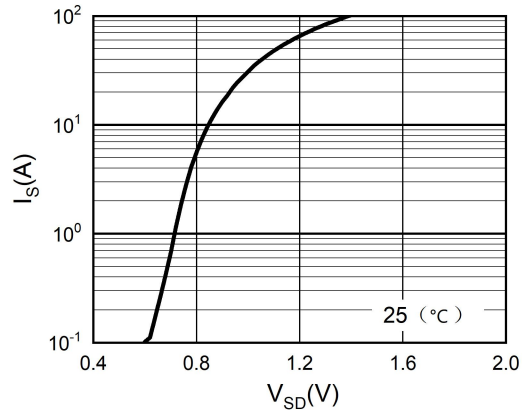
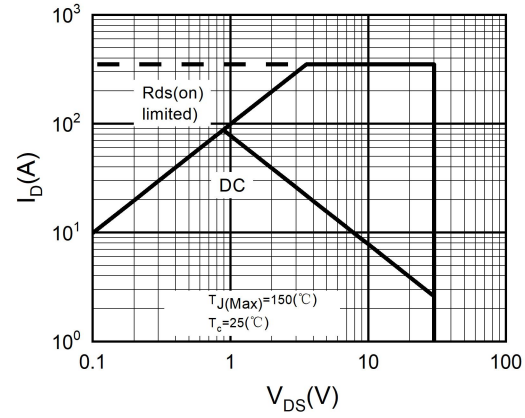
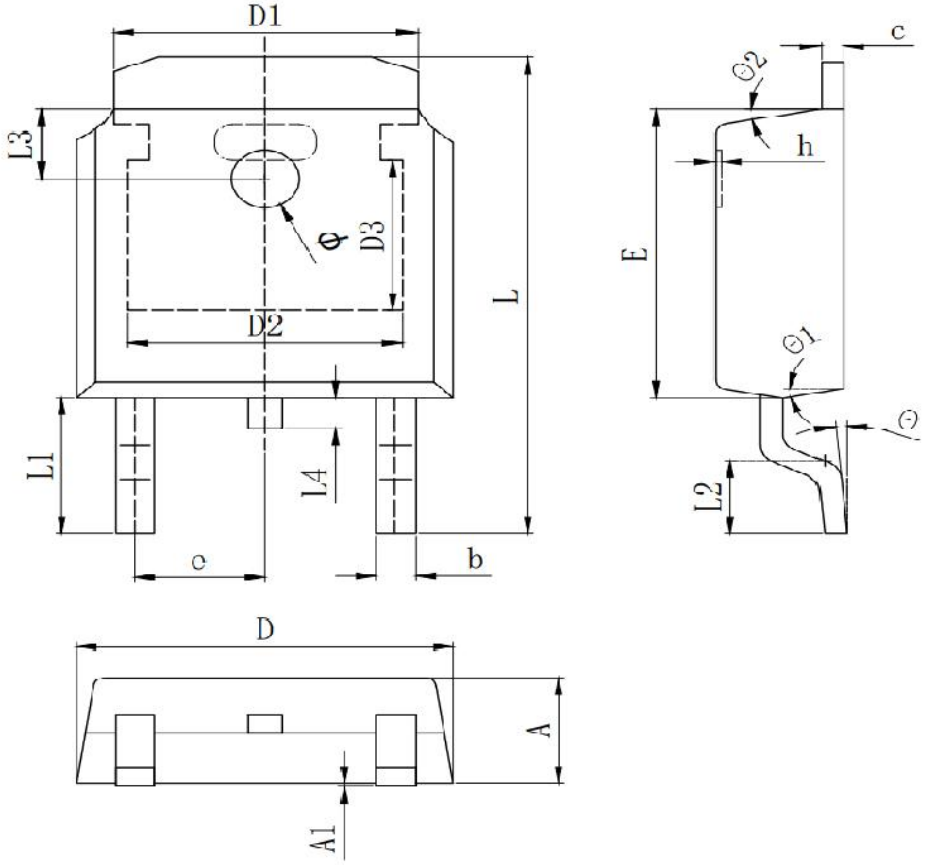


Figure 10. Maximum Safe Operating Area



TO-252 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

Attention

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